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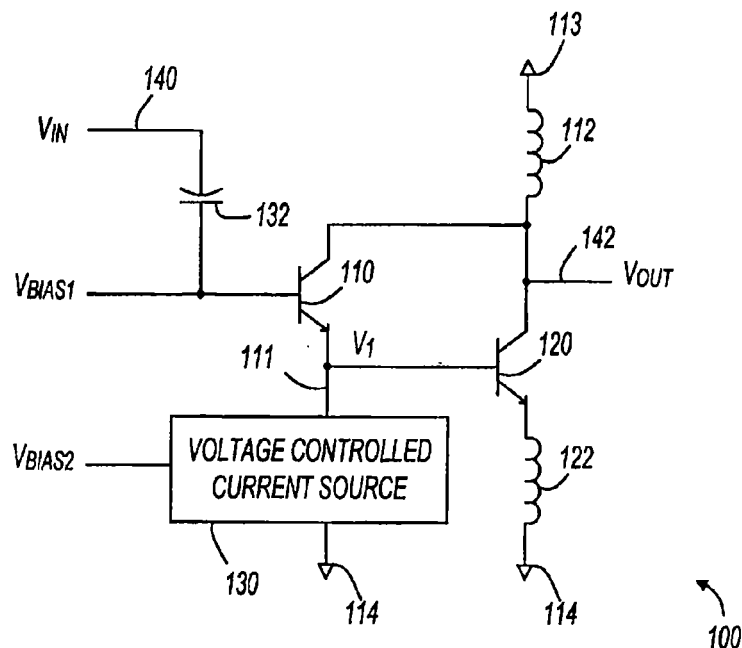
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(54) Title: BIASED DARLINGTON TRANSISTOR PAIR, METHOD, AND SYSTEM



(57) Abstract: An amplifier includes a Darlington transistor pair (110, 120) and a biasing network to increase bias currents in an input transistor (110). Circuit (100) includes in put transistor (110), second transistor (120), radio frequency (RF) choke (112), degeneration inductor (122), capacitor (132) and voltage controlled current source (130). Input transistor (110) and second transistor (120) are coupled to form a Darlington transistor pair with the collectors coupled together at node (142), and the emitter of input transistor (120) at node (111).



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